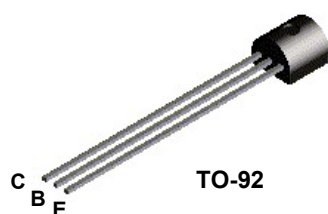


2N4403



MMBT4403



PNP General Purpose Amplifier

This device is designed for use as a general purpose amplifier and switch requiring collector currents to 500 mA.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	40	V
V _{CBO}	Collector-Base Voltage	40	V
V _{EBO}	Emitter-Base Voltage	5.0	V
I _C	Collector Current - Continuous	600	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max		Units
		2N4403	*MMBT4403	
P _D	Total Device Dissipation	625	350	mW
	Derate above 25°C	5.0	2.8	mW/°C
R _{θJC}	Thermal Resistance, Junction to Case	83.3		°C/W
R _{θJA}	Thermal Resistance, Junction to Ambient	200	357	°C/W

*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

PNP General Purpose Amplifier

(continued)

2N4403 / MMBT4403

Electrical Characteristics

TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
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OFF CHARACTERISTICS

$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	$I_C = 1.0 \text{ mA}, I_B = 0$	40		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 0.1 \text{ mA}, I_E = 0$	40		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 0.1 \text{ A}, I_C = 0$	5.0		V
I_{BEX}	Base Cutoff Current	$V_{CE} = 35 \text{ V}, V_{EB} = 0.4 \text{ V}$		0.1	μA
I_{CEX}	Collector Cutoff Current	$V_{CE} = 35 \text{ V}, V_{BE} = 0.4 \text{ V}$		0.1	μA

ON CHARACTERISTICS

h_{FE}	DC Current Gain	$I_C = 0.1 \text{ mA}, V_{CE} = 1.0 \text{ V}$ $I_C = 1.0 \text{ mA}, V_{CE} = 1.0 \text{ V}$ $I_C = 10 \text{ mA}, V_{CE} = 1.0 \text{ V}$ $I_C = 150 \text{ mA}, V_{CE} = 2.0 \text{ V}^*$ $I_C = 500 \text{ mA}, V_{CE} = 2.0 \text{ V}^*$	30 60 100 100 20	300	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage*	$I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$ $I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$		0.4 0.75	V V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 150 \text{ mA}, I_B = 15 \text{ mA}^*$ $I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$	0.75	0.95 1.3	V V

SMALL SIGNAL CHARACTERISTICS

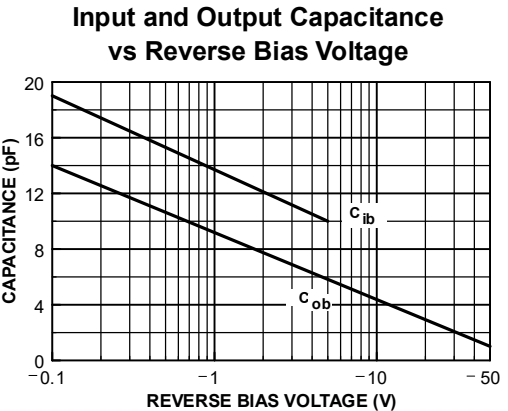
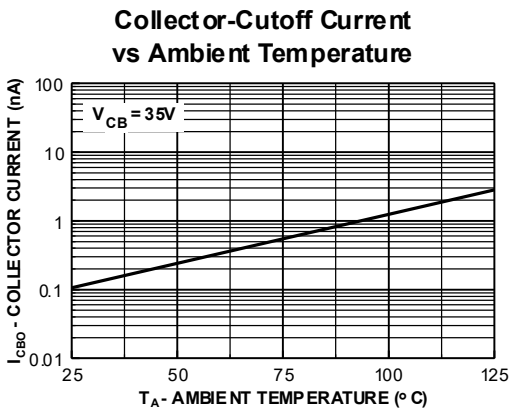
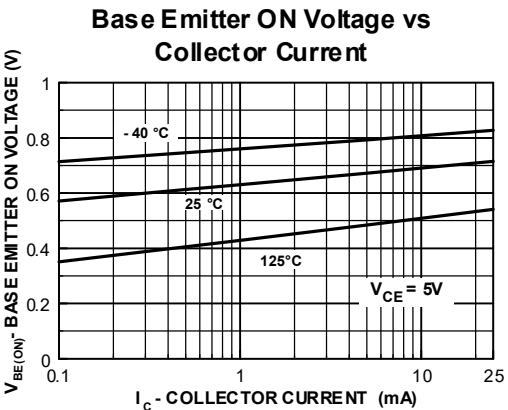
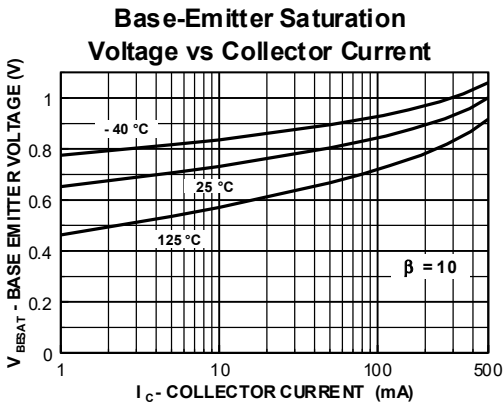
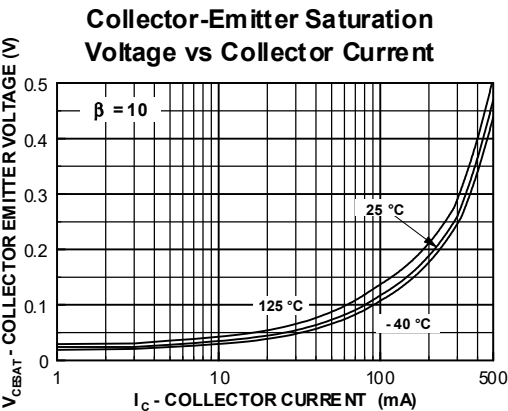
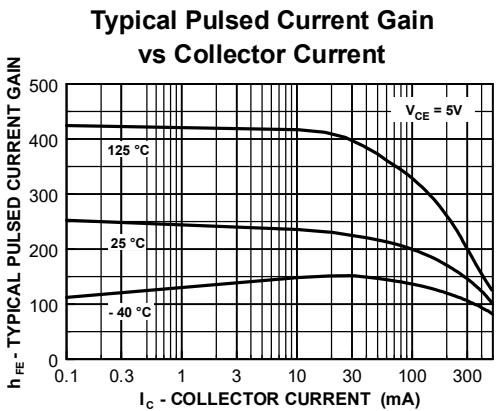
f_T	Current Gain - Bandwidth Product	$I_C = 20 \text{ mA}, V_{CE} = 10 \text{ V},$ $f = 100 \text{ MHz}$	200		MHz
C_{cb}	Collector-Base Capacitance	$V_{CB} = 10 \text{ V}, I_E = 0,$ $f = 140 \text{ kHz}$		8.5	pF
C_{eb}	Emitter-Base Capacitance	$V_{BE} = 0.5 \text{ V}, I_C = 0,$ $f = 140 \text{ kHz}$		30	pF
h_{ie}	Input Impedance	$I_C = 1.0 \text{ mA}, V_{CE} = 10 \text{ V},$ $f = 1.0 \text{ kHz}$	1.5	15	$k\Omega$
h_{re}	Voltage Feedback Ratio	$I_C = 1.0 \text{ mA}, V_{CE} = 10 \text{ V},$ $f = 1.0 \text{ kHz}$	0.1	8.0	$\times 10^{-4}$
h_{fe}	Small-Signal Current Gain	$I_C = 1.0 \text{ mA}, V_{CE} = 10 \text{ V},$ $f = 1.0 \text{ kHz}$	60	500	
h_{oe}	Output Admittance	$I_C = 1.0 \text{ mA}, V_{CE} = 10 \text{ V},$ $f = 1.0 \text{ kHz}$	1.0	100	μmhos

SWITCHING CHARACTERISTICS

t_d	Delay Time	$V_{CC} = 30 \text{ V}, I_C = 150 \text{ mA},$		15	ns
t_r	Rise Time	$I_{B1} = 15 \text{ mA}$		20	ns
t_s	Storage Time	$V_{CC} = 30 \text{ V}, I_C = 150 \text{ mA}$		225	ns
t_f	Fall Time	$I_{B1} = I_{B2} = 15 \text{ mA}$		30	ns

*Pulse Test: Pulse Width $\leq 300 \text{ ms}$, Duty Cycle $\leq 2.0\%$

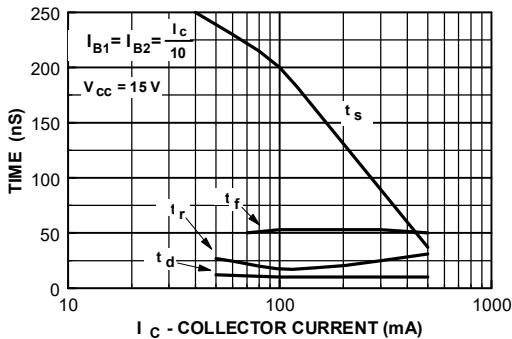
Typical Characteristics



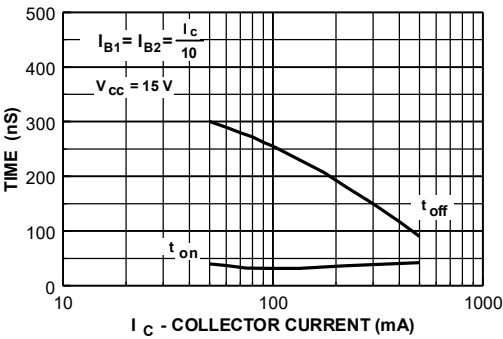
PNP General Purpose Amplifier
(continued)

Typical Characteristics (continued)

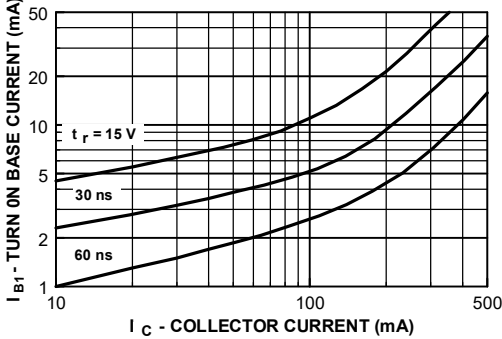
Switching Times
vs Collector Current



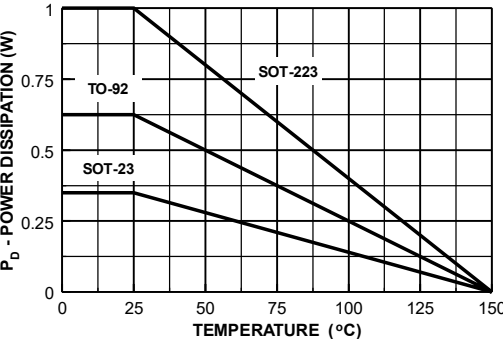
Turn On and Turn Off Times
vs Collector Current



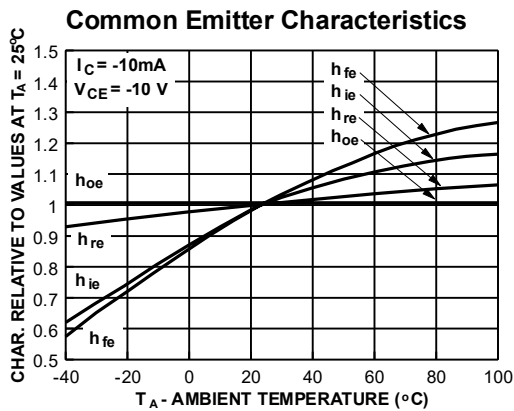
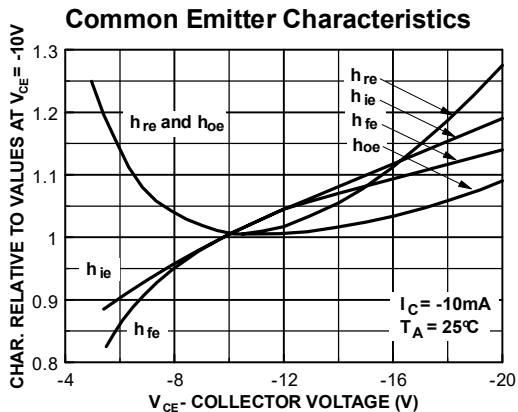
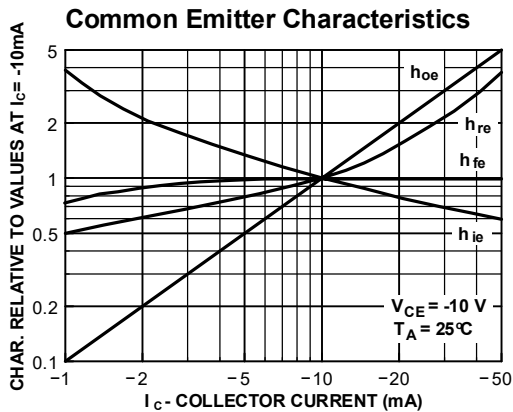
Rise Time vs Collector
and Turn On Base Currents



Power Dissipation vs
Ambient Temperature



Typical Common Emitter Characteristics (f = 1.0kHz)



Test Circuits

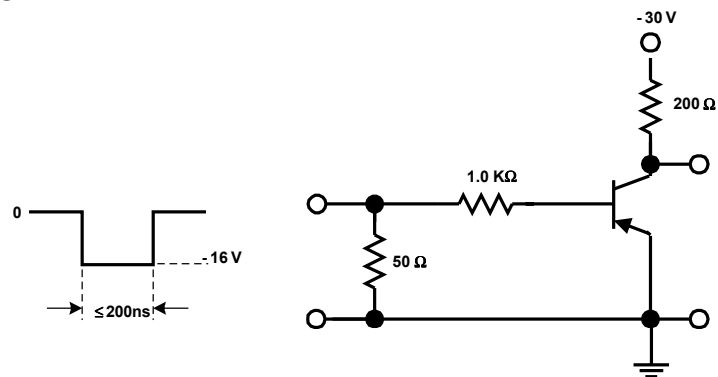


FIGURE 1: Saturated Turn-On Switching Time Test Circuit

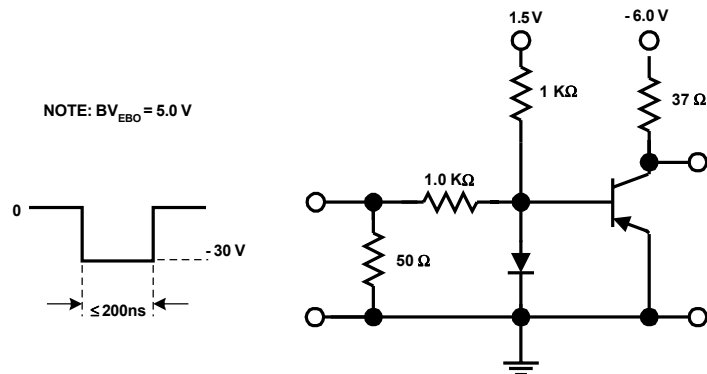


FIGURE 2: Saturated Turn-Off Switching Time Test Circuit

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DOME™	HiSeC™	PowerTrench [®]	SuperSOT™-8	
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E ² CMOS™	LittleFET™	QS™	TinyLogic™	
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